

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1485	(phase adj change) with (electrode plate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:00
L2	618	1 and ((recess trench hole via groove opening) with (plate electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:01
L3	492	1 and ((recess trench hole via groove opening) near5 (plate electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:01
L4	471	1 and ((recess trench hole via groove opening) near4 (plate electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:01
L5	259	1 and ((recess trench hole via groove opening) near4 (electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:01
L6	234	1 and ((recess trench hole via groove opening) near3 (electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:02
L7	193	1 and ((recess trench hole via groove opening) near2 (electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:02
L8	80	1 and ((recess trench hole via groove opening) near (electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:46
L9	1	"5534711".PN.	USPAT; USOCR	OR	ON	2005/05/11 07:05
L10	25320	(recess trench hole via groove) near (electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:58

L11	440459	capacitor (recess trench hole via groove) near (electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:58
L12	1780	capacitor with (recess trench hole via groove) near (electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:59
L14	639	((recess trench hole via groove) near3 (phase near3 change))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:00
L15	0	12 and 14	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:00
L16	1	((recess trench hole via groove) near3 (phase near3 change)) with capacitor	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:01
L17	1	((recess trench hole via groove damascene) near3 (phase near3 change)) with capacitor	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:02
L18	642	((recess trench hole via groove damascene) near3 (phase near3 change))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:02
L19	33	18 and ((recess trench hole via groove damascene) near3 (electrode))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:02
L20	1	"6605527".PN.	USPAT; USOCR	OR	ON	2005/05/11 08:33
L21	1	"6511862".PN.	USPAT; USOCR	OR	ON	2005/05/11 08:34
L22	667	(recess trench hole via groove opening) near3 (phase adj change chalcogenide phase-change ovonic)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:47
L23	88	22 and (recess trench hole via groove opening) near3 (electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 08:48

S32	185	(phase adj change) with capacitor	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:00
S33	1482	(phase adj change) with memory	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:16
S35	1661	S32 or S33	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:16
S36	1661	S35 and (phase adj change capacitor memory)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:23
S37	416	"22" and ((phase adj change with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:19
S38	182	S36 and ((phase adj change with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:19
S39	121	S38 and ((recess trench hole via groove opening) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/05/11 07:00
S40	131	S38 and ((recess trench hole via groove opening pore damascene) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:23
S41	2081	438/259,270.ccls.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:22
S42	0	S41 and S36	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:22
S43	592	S41 and (phase adj change capacitor memory)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:23

S44	246	S43 and ((recess trench hole via groove opening pore damascene) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:58
S45	2	S43 and (phase adj change)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:59
S46	0	S41 and ((phase adj change) with (memory capaitor material layer))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 15:00
S47	10493	((phase adj change) with (memory capaitor material layer))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 15:01
S48	40	((phase adj change) with (memory capaitor material layer)) with (electrode near5 (recess trench pore damascene hole opening groove aperture))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 15:03